

4-BIT SINGLE-CHIP MICROCONTROLLER

The μPD17P104 is a tiny microcontroller consisting of a 1K-byte ROM, 16-word RAM, and 16 input/output ports. It is a one-time PROM version of the μPD17104, whose internal mask ROM is replaced with a one-time PROM.

Two μPD17P104 models are available: μPD17P104CS and μPD17P104GS, which allow a program to be written only once. They are suitable for evaluation of μPD17104 and for small-scale production.

The μPD17000 architecture of the CPU uses general registers so that data memory can be manipulated directly for effective programming. Every instruction is 1 word long, consisting of 16 bits.

FEATURES

- Compatible with the μPD17104
- Program memory (one-time PROM): 1K bytes (512 words x 16 bits)
- Data memory (RAM): 16 words x 4 bits
- Input/output ports: 16 ports (including four N-ch open-drain outputs)
- Instruction execution time: 2 μs (with 8 MHz crystal or ceramic resonator connected)
- Number of instructions: 24 (Each instruction is 1 word long.)
- Stack level: 1
- A standby function is supported (with the STOP and HALT instructions).
- Data memory can retain data on low voltage (2.0 V at minimum).
- An oscillator is included for the system clock (for crystal or ceramic resonator).
- Operating supply voltage: 2.7 to 6.0 V (at 2 MHz)
4.5 to 6.0 V (at 8 MHz)

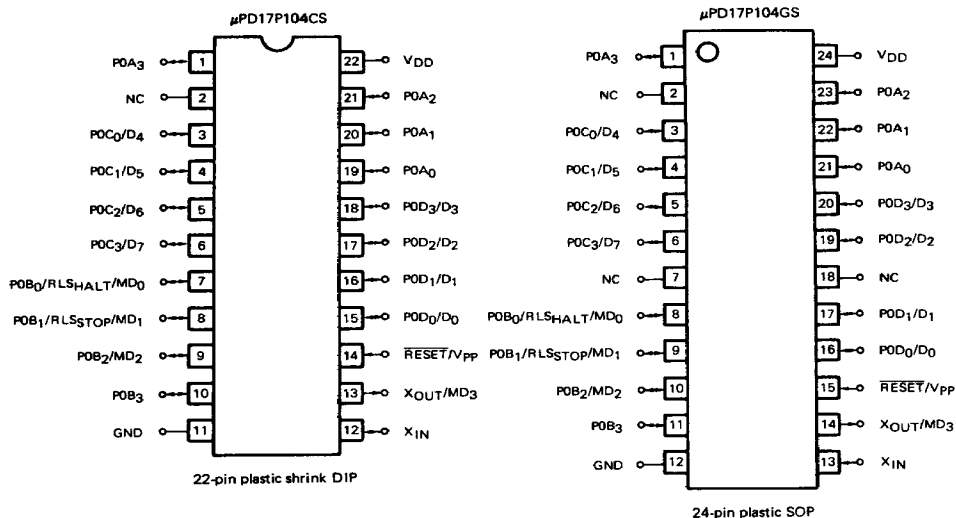
APPLICATIONS

- Controlling electric appliances or toys
- Providing general-purpose logic ICs in one chip

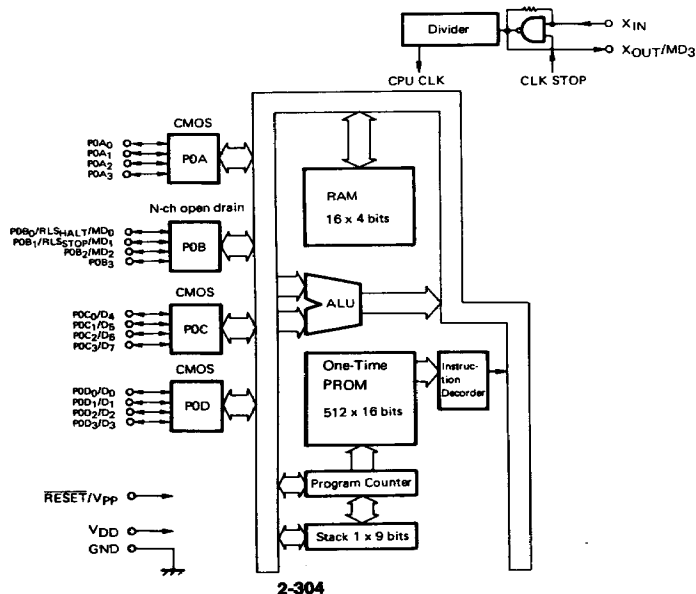
ORDERING INFORMATION

Order Code	Package
μPD17P104CS	22-pin plastic shrink DIP (300 mil)
μPD17P104GS	24-pin plastic SOP (300 mil)

PIN CONFIGURATION (Top View)



BLOCK DIAGRAM



PIN FUNCTIONS

• Port pins

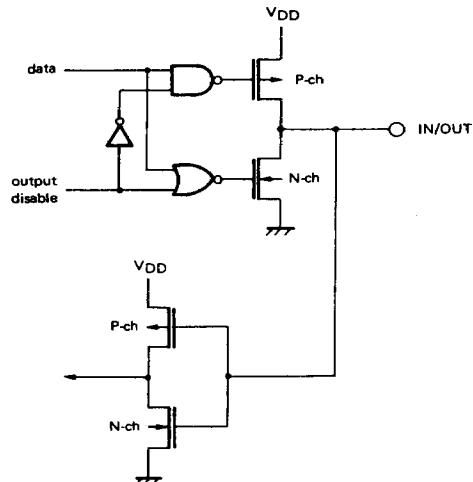
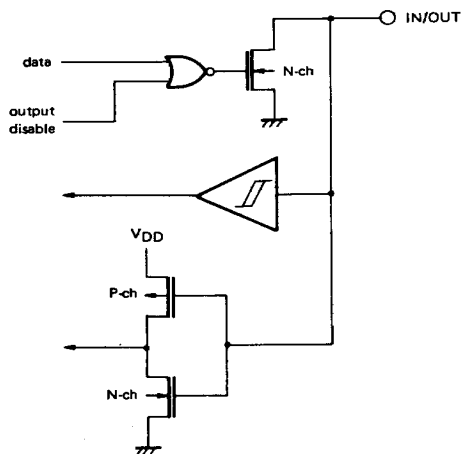
PIN NAME	INPUT/ OUTPUT	DUAL FUNCTION PIN		FUNCTION		When writing to program memory or verifying its contents	WHEN RESET
P0A0	Input/output			• CMOS (push-pull) 4-bit input/ output port (port 0A)		Pull down	High impedance (input mode)
P0A1							
P0A2							
P0A3							
P0B0	Input/output	RLSHALT	MD0	• N-ch open-drain 4-bit input/ output port (port 0B)	For the HALT mode releasing	Mode selection pin	High impedance (input mode)
P0B1		RLSSTOP	MD1		For the STOP mode releasing		
P0B2		MD2					
P0B3					Pull down		
P0C0		Input/output	D4		• CMOS (push-pull) 4-bit input/ output port (port 0C)	8-bit data input/output pin (high-order 4 bits)	
P0C1	D5						
P0C2	D6						
P0C3	D7						
P0D0	Input/output	D0		• CMOS (push-pull) 4-bit input/ output port (port 0D)	8-bit data input/output pin (low-order 4-bits)	High impedance (input mode)	
P0D1		D1					
P0D2		D2					
P0D3		D3					

• Non-port pins

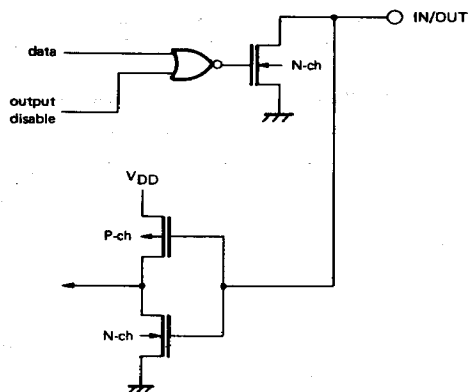
PIN NAME	INPUT/ OUTPUT	DUAL FUNCTION PIN	FUNCTION	When writing to program memory or verifying its contents
RESET	Input	V _{pp}	System reset input pin	Voltage is applied to this pin (+12.5 V)
V _{DD}			Positive power supply pin	Positive power supply pin (+6.0 V)
GND			GND pin	GND pin
X ₁ IN			Pins to be connected to the system clock resonator	Program memory address update
X ₂ OUT		MD ₃	Pins to be connected to the system clock resonator	Mode selection pin
NC			NC pin is not connected internally.	

PIN INPUT/OUTPUT CIRCUITS

Following are schematics of the input/output circuits of the pins of the μ PD17P104.

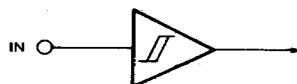
(1) P0C and P0D**(2) P0B₀ and P0B₁**

(3) P0B₂ and P0B₃



2

(4) RESET



9. DIFFERENCES BETWEEN THE μPD17P104 AND μPD17104

The μPD17P104 is a one-time PROM version of the μPD17104, in which the internal mask ROM is replaced with a one-time PROM. The μPD17P104 has the same CPU functions and internal hardwares as those of μPD17104 except for its program memory and mask option. Table 9-1 lists the differences between them.

Table 9-1 Differences between μPD17P104 and μPD17104

ITEM	μPD17P104	μPD17104
ROM	One-time PROM 512 x 16 bits	Mask ROM 512 x 16 bits
Pull-up resistors of pins P0B ₀ to P0B ₃	None	Mask option
Pull-up resistors of RESET pin	None	Mask option
Connection pin	V _{PP} pin and operation mode selection pins are provided.	V _{PP} pin and operation mode selection pins are not provided.
Power supply	2.7 to 6.0 V (at 2 MHz) 4.5 to 6.0 V (at 8 MHz)	
Package	22-pin plastic shrink DIP 24-pin plastic SOP	
Waiting time for the operation mode	16 clock pulses	8 clock pulses

10. WRITING TO AND VERIFYING ONE-TIME PROM (PROGRAM MEMORY)

The μPD17P104's internal program memory consists of a 512 x 16 bit one-time PROM.

Writing to the one-time PROM or verifying the contents of the PROM is accomplished using the pins shown in the table below. Note that address inputs are not used; instead, the address is updated using the clock input from the X_{IN} pin.

PIN NAME	FUNCTION
V _{PP}	Voltage is applied to this pin when writing to program memory or verifying its contents.
X _{IN}	Input pin for address update clock used when writing to program memory or verifying its contents
MD ₀ to MD ₃	Pins that turn to input pins and are used as operation mode selection pins when writing to program memory or verifying its contents
D ₀ to D ₇	Input/output pins for 8-bit data used when writing to program memory or verifying its contents

10.1 PROGRAM MEMORY WRITE/VERIFY MODES

If +6 V is applied to the V_{DD} pin and +12.5 V is applied to the V_{PP} pin after a certain duration of reset status (V_{DD} = 5 V, RESET = 0 V), the μPD17P104 enters program memory write/verify mode. A specific operating mode is then selected by setting the MD₀ through MD₃ pins as follows. Set the other unused pins to GND level by means of pull-down resistors.

OPERATING MODE SPECIFICATION						OPERATING MODE
V _{PP}	V _{DD}	MD ₀	MD ₁	MD ₂	MD ₃	
+12.5 V	+6 V	H	L	H	L	Program memory address clear mode
		L	H	H	H	Write mode
		L	L	H	H	Verify mode
		H	X	H	H	Program inhibit mode

X: L (low) or H (high)

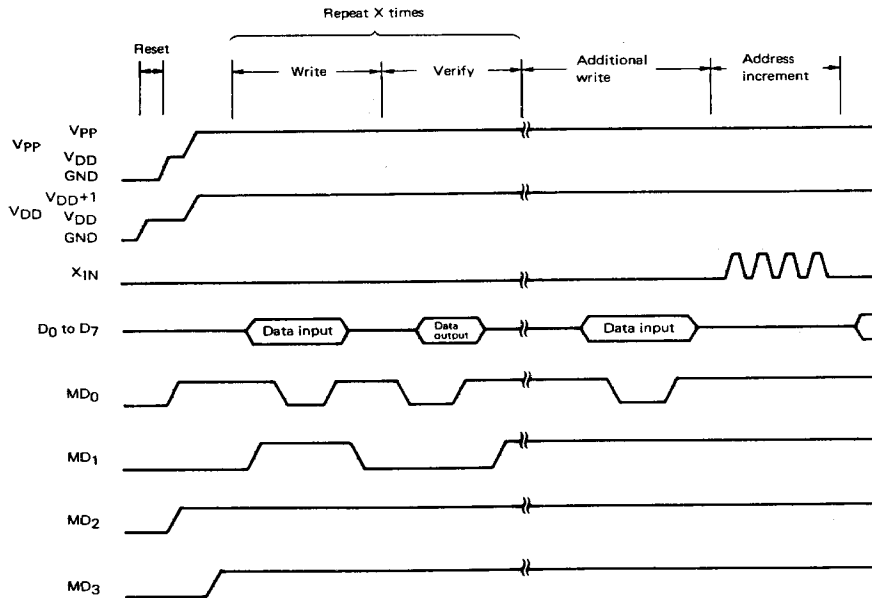
10.2 WRITING TO PROGRAM MEMORY

The procedure for writing to program memory is described below; high-speed write is possible.

- (1) Pull low the levels on all unused pins to GND by means of resistors. Bring X_{IN} to low level.
- (2) Apply 5 V to V_{DD} and bring V_{PP} to low level.
- (3) Wait 10 μs. Then apply 5 V to V_{PP}.
- (4) Set the mode selection pins to program memory address clear mode.
- (5) Apply 6 V to V_{DD} and 12.5 V to V_{PP}.
- (6) Select program inhibit mode.
- (7) Write data in 1 ms write mode.
- (8) Select program inhibit mode.
- (9) Select verify mode. If the write operation is found successful, proceed to step (10). If the operation is found unsuccessful, repeat steps (7) to (9).
- (10) Perform additional write for (number of repetitions of steps (7) to (9)) x 1 ms.
- (11) Select program inhibit mode.

- (12) Increment the program memory address by one on reception of four pulses on the X_{IN} pin.
- (13) Repeat steps (7) to (12) until the last address is reached.
- (14) Select program memory address clear mode.
- (15) Apply 5 V to the V_{DD} and V_{PP} pins.
- (16) Turn power off.

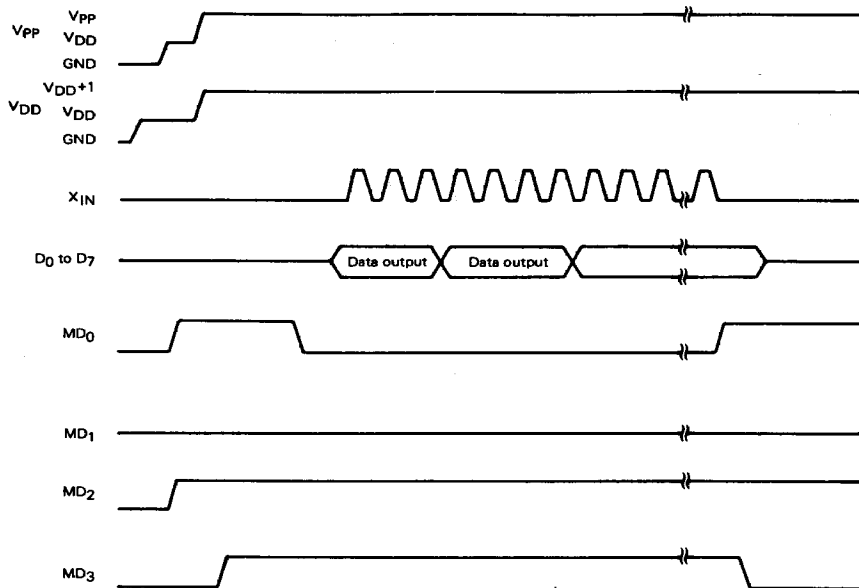
The timing for steps (2) to (12) is shown below.



10.3 READING PROGRAM MEMORY

- (1) Pull low the levels of all unused pins to GND by means of resistors. Bring X_{IN} to low level.
- (2) Apply 5 V to V_{DD} and bring V_{PP} to low level.
- (3) Wait 10 μ s. Then apply 5 V to V_{PP} .
- (4) Set the mode selection pins to program memory address clear mode.
- (5) Apply 6 V to V_{DD} and 12.5 V to V_{PP} .
- (6) Select program inhibit mode.
- (7) Select verify mode. Data is output sequentially one address at a time for each cycle of four clock pulses on the X_{IN} pin.
- (8) Select program inhibit mode.
- (9) Select program memory address clear mode.
- (10) Apply 5 V to the V_{DD} and V_{PP} pins.
- (11) Turn power off.

The timing for steps (2) to (9) is shown below.



11. ASSEMBLER RESERVED WORDS

Table 11-1 lists the reserved words defined in the μPD17P104 device file (AS17104).

Table 11-1 Reserved Words

Name	Attribute	Value	Read/write	Description
P0A0	FLG	0.70H.0	Read/write	Bit 0 of port 0A
P0A1	FLG	0.70H.1	Read/write	Bit 1 of port 0A
P0A2	FLG	0.70H.2	Read/write	Bit 2 of port 0A
P0A3	FLG	0.70H.3	Read/write	Bit 3 of port 0A
P0B0	FLG	0.71H.0	Read/write	Bit 0 of port 0B
P0B1	FLG	0.71H.1	Read/write	Bit 1 of port 0B
P0B2	FLG	0.71H.2	Read/write	Bit 2 of port 0B
P0B3	FLG	0.71H.3	Read/write	Bit 3 of port 0B
P0C0	FLG	0.72H.0	Read/write	Bit 0 of port 0C
P0C1	FLG	0.72H.1	Read/write	Bit 1 of port 0C
P0C2	FLG	0.72H.2	Read/write	Bit 2 of port 0C
P0C3	FLG	0.72H.3	Read/write	Bit 3 of port 0C
P0D0	FLG	0.73H.0	Read/write	Bit 0 of port 0D
P0D1	FLG	0.73H.1	Read/write	Bit 1 of port 0D
P0D2	FLG	0.73H.2	Read/write	Bit 2 of port 0D
P0D3	FLG	0.73H.3	Read/write	Bit 3 of port 0D
BCD	FLG	0.7EH.0	Read/write	BCD arithmetic flag
PSW	MEM	0.7FH	Read/write	Program status word
Z	FLG	0.7FH.1	Read/write	Zero flag
CY	FLG	0.7FH.2	Read/write	Carry flag
CMP	FLG	0.7FH.3	Read/write	Compare flag

12. INSTRUCTION SET

12.1 INSTRUCTION SET LIST

b ₁₄ to b ₁₁		b ₁₅			0	1
BIN	HEX					
0 0 0 0	0		ADD	r, m	ADD	m, #i
0 0 0 1	1		SUB	r, m	SUB	m, #i
0 0 1 0	2		ADDC	r, m	ADDC	m, #i
0 0 1 1	3		SUBC	r, m	SUBC	m, #i
0 1 0 0	4		AND	r, m	AND	m, #i
0 1 0 1	5		XOR	r, m	XOR	m, #i
0 1 1 0	6		OR	r, m	OR	m, #i
0 1 1 1	7		RET			
			RETSK			
			RORC	r		
			STOP	s		
			HALT	h		
			NOP			
1 0 0 0	8		LD	r, m	ST	m, r
1 0 0 1	9		SKE	m, #i	SKGE	m, #i
1 0 1 0	A					
1 0 1 1	B		SKNE	m, #i	SKLT	m, #i
1 1 0 0	C		BR	addr	CALL	addr
1 1 0 1	D				MOV	m, #i
1 1 1 0	E				SKT	m, #n
1 1 1 1	F				SKF	m, #n

12.2 INSTRUCTIONS

Legend:

M	: One of data memory	n	: Bit position : 4 bits
m	: Data memory address specified by $[m_H, m_L]$ of each bank	addr	: One of program memory address : 11 bits
m_H	: Data memory address high (row address) : 3 bits	a_H	: Program memory address high : 3 bits
m_L	: Data memory address low (column address) : 4 bits	a_M	: Program memory address middle : 4 bits
R	: One of general register specified by $[(RP), r]$	a_L	: Program memory address low : 4 bits
r	: General register address low (column address) : 4 bits	CY	: Carry flag
RP	: General register pointer	CMP	: Compare flag
PC	: Program counter	s	: Stop release condition
SP	: Stack pointer	h	: Halt release condition
STACK	: Stack specified by (SP)	[]	: Address of M, R
i	: Immediate data : 4 bits	()	: Contents of M, R

Type	Mnemonic	Operand	Function	Operation	Machine code			
					Op code	3 bits	4 bits	4 bits
Add	ADD	r, m	Add memory to register	$R \leftarrow (R) + (M)$	0000	m_H	m_L	r
		m, #i	Add immediate data to memory	$M \leftarrow (M) + i$	1000	m_H	m_L	i
	ADDC	r, m	Add memory to register with carry	$R \leftarrow (R) + (M) + (CY)$	0001	m_H	m_L	r
		m, #i	Add immediate data to memory with carry	$R \leftarrow (M) + i + (CY)$	1001	m_H	m_L	i
Subtract	SUB	r, m	Subtract memory from register	$R \leftarrow (R) - (M)$	0000	m_H	m_L	r
		m, #i	Subtract immediate data from memory	$M \leftarrow (M) - i$	1000	m_H	m_L	i
	SUBC	r, m	Subtract memory from register with borrow	$R \leftarrow (R) - (M) - (CY)$	0001	m_H	m_L	r
		m, #i	Subtract immediate data from memory with borrow	$M \leftarrow (M) - i - (CY)$	1001	m_H	m_L	i
Compare	SKE	m, #i	Skip if memory equal to immediate data	$M - i$, skip if zero	0100	m_H	m_L	i
	SKGE	m, #i	Skip if memory greater than or equal to immediate data	$M - i$, skip if not borrow	1100	m_H	m_L	i
	SKLT	m, #i	Skip if memory less than immediate data	$M - i$, skip if borrow	1101	m_H	m_L	i
	SKNE	m, #i	Skip if memory not equal to immediate data	$M - i$, skip if not zero	0101	m_H	m_L	i
Logical operation	AND	m, #i	Logical AND of memory and immediate data	$M \leftarrow (M) \text{ AND } i$	1010	m_H	m_L	i
		r, m	Logical AND of register and memory	$R \leftarrow (R) \text{ AND } (M)$	0010	m_H	m_L	r
	OR	m, #i	Logical OR of memory and immediate data	$M \leftarrow (M) \text{ OR } i$	1011	m_H	m_L	i
		r, m	Logical OR of register and memory	$R \leftarrow (R) \text{ OR } (M)$	0011	m_H	m_L	r
	XOR	m, #i	Logical XOR of memory and immediate data	$M \leftarrow (M) \text{ XOR } i$	1010	m_H	m_L	i
		r, m	Logical XOR of register and memory	$R \leftarrow (R) \text{ XOR } (M)$	0011	m_H	m_L	r
Transfer	LD	r, m	Load memory of register	$R \leftarrow (M)$	0100	m_H	m_L	r
	ST	m, r	Store register to memory	$(M) \leftarrow R$	1100	m_H	m_L	r
	MOV	m, #i	Move immediate data to memory	$M \leftarrow i$	1101	m_H	m_L	i
Test	SKT	m, #n	Test memory bits, then skip if all bits specified are true	$CMP \leftarrow 0$ skip if $M_n = \text{all "1"}$	1110	m_H	m_L	n
	SKF	m, #n	Test memory bits, then skip if all bits specified are false	$CMP \leftarrow 0$ skip if $M_n = \text{all "0"}$	1111	m_H	m_L	n

Type	Mnemonic	Operand	Function	Operation	Machine code			
					Op code	3 bits	4 bits	4 bits
Branch	BR	addr	Jump to the address	PC←ADDR	01100	a _H	a _M	a _L
Shift	RORC	r	Rotate register right with carry	(CY)→(R)→CY	00111	000	0111	r
Subroutine	CALL	addr	Call subroutine	SP←(SP) - 1 STACK←((PC) + 1), PC←ADDR	11100	a _H	a _M	a _L
	RET		Return to main routine from subroutine	PC←(STACK), SP←(SP) + 1	00111	000	1110	0000
	RETSK		Return to main routine from subroutine, then skip unconditional	PC←(STACK), SP←(SP) + 1 and skip	00111	001	1110	0000
Miscellaneous	STOP	s	Stop clock	STOP	00111	010	1111	s
	HALT	h	Halt the CPU, restart by condition h	HALT	00111	011	1111	h
	NOP		No operation	No Operation	00111	100	1111	0000

13. ELECTRICAL CHARACTERISTICS (PRELIMINARY)**ABSOLUTE MAXIMUM RATINGS ($T_a = 25^\circ\text{C}$)**

Supply Voltage	V_{DD}		−0.3 to +7.0	V
Supply Voltage	V_{PP}		−0.3 to +13.5	V
Input Voltage	V_I	P0A, P0C, P0D	−0.3 to $V_{DD}+0.3$	V
		P0B	−0.3 to +11	V
Output Voltage	V_O	P0A, P0C, P0D	−0.3 to $V_{DD}+0.3$	V
		P0B	−0.3 to +11	V
High-Level Output Current	I_{OH}	Each of P0A, P0B, P0C, P0D	−5	mA
		Total of all pins	−15	mA
Low-Level Output Current	I_{OL}	Each of P0A, P0B, P0C, P0D	30	mA
		Total of all pins	100	mA
Operating Temperature	T_{opt}		−40 to +85	$^\circ\text{C}$
Storage Temperature	T_{stg}		−65 to +150	$^\circ\text{C}$
Power Consumption	P_d	$T_a = 85^\circ\text{C}$ 22-pin shrink DIP	400	mW
		24-pin SOP	250	

CAPACITANCE ($T_a = 25^\circ\text{C}$, $V_{DD} = 0\text{ V}$)

CHARACTERISTICS	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS
Input Capacitance	C_{IN}			15	pF	$f = 1\text{ MHz}$ 0 V for pins other than pins to be measured
I/O(*) Capacitance	C_{IO}			15	pF	

* Input/output

DC CHARACTERISTICS (T_a = -40 to +85 °C, V_{DD} = 2.7 to 6.0 V)

CHARACTERISTICS	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS	
High-Level Input Voltage	V _{IH1}	0.7 V _{DD}		V _{DD}	V	Other than the following pins and port	
	V _{IH2}	0.8 V _{DD}		V _{DD}	V	P0B and RESET	
	V _{IH3}	0.8 V _{DD}		9	V	P0B	(*)
	V _{IH4}	V _{DD} -0.5		V _{DD}	V	X _{IN}	
Low-Level Input Voltage	V _{IL1}	0		0.3 V _{DD}	V	Other than the following pins and port	
	V _{IL2}	0		0.2 V _{DD}	V	P0B and RESET	
	V _{IL3}	0		0.5	V	X _{IN}	
High-Level Output Voltage on P0A, P0C, and P0D	V _{OH}	V _{DD} -2.0			V	V _{DD} = 4.5 to 6.0 V, I _{OH} = -2 mA	
		V _{DD} -1.0			V	I _{OH} = -200 μA	
Low-Level Output Voltage on P0A, P0B, P0C, and P0D	V _{OL}			2.0	V	V _{DD} = 4.5 to 6.0 V, I _{OL} = 15 mA	
				0.5	V	I _{OL} = 600 μA	
High-Level Input Leakage Current on P0A to P0D	I _{LIH1}			5	μA	V _{IN} = V _{DD}	
	I _{LIH2}			10	μA	V _{IN} = 9 V	
Low-Level Input Leakage Current on P0A to P0D	I _{LIL}			-5	μA	V _{IN} = 0 V	
High-Level Output Leakage Current on P0A to P0D	I _{LOH1}			5	μA	V _{OUT} = V _{DD}	
	I _{LOH2}			10	μA	V _{OUT} = 9 V	
Low-Level Output Leakage Current on P0A to P0D	I _{LOL}			-5	μA	V _{OUT} = 0 V	
Power Supply Current	I _{DD1}		1.5	4.5	mA	Operation mode	V _{DD} = 5 V ± 10 %, f _{CC} = 8.0 MHz
			250	750	μA		V _{DD} = 3 V ± 10 %, f _{CC} = 2.0 MHz
	I _{DD2}		1.0	3.0	mA	HALT mode	V _{DD} = 5 V ± 10 %, f _{CC} = 8.0 MHz
			200	600	μA		V _{DD} = 3 V ± 10 %, f _{CC} = 2.0 MHz
	I _{DD3}		0.1	10	μA	STOP mode	V _{DD} = 5 V ± 10 %
			0.1	5	μA		V _{DD} = 3 V ± 10 %

* When N-ch open-drain input/output is selected

**CHARACTERISTICS OF DATA MEMORY FOR HOLDING DATA ON LOW SUPPLY VOLTAGE
IN THE STOP MODE ($T_a = -40$ to $+85$ °C)**

CHARACTERISTICS	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS
Data Hold Supply Voltage	V _{DDDR}	2.0		6.0	V	
Data Hold Supply Current	I _{DDDR}		0.1	5.0	μ A	V _{DDDR} = 2.0 V
Release Signal Set Time	t _{SREL}	0			μ s	

AC CHARACTERISTICS ($T_a = -40$ to $+85$ °C, V_{DD} = 2.7 to 6.0 V)

CHARACTERISTICS	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS
Internal Clock Cycle Time	T _{CY}	1.9		33	μ s	V _{DD} = 4.5 to 6.0 V
		7.6		33	μ s	
High/Low Level Width on POB ₀ and POB ₁	T _{PBH} T _{PBL}	10			μ s	
High/Low Level Width on RESET	T _{RSH} T _{RSL}	10			μ s	

DC PROGRAMING CHARACTERISTICS ($T_a = 25$ °C, V_{DD} = 6.0 $\pm$ 0.25 V, V_{pp} = 12.5 $\pm$ 0.5 V)

CHARACTERISTICS	SYMBOL	MIN.	TYP.	MAX.	UNIT	CONDITIONS
Input Voltage High	V _{IH1}	0.7 V _{DD}		V _{DD}	V	Except X _{IN}
	V _{IH2}	V _{DD} -0.5		V _{DD}	V	X _{IN}
Input Voltage Low	V _{IL1}	0		0.3 V _{DD}	V	Except X _{IN}
	V _{IL2}	0		0.4	V	X _{IN}
Input Leakage Current	I _{LI}			10	μ A	V _{IN} = V _{IL} or V _{IH}
Output Voltage High	V _{OH}	V _{DD} -1.0			V	I _{OH} = -1 mA
Output Voltage Low	V _{OL}			0.4	V	I _{OL} = 1.6 mA
V _{DD} Power Supply Current	I _{DD}			30	mA	
V _{pp} Power Supply Current	I _{pp}			30	mA	MD0 = V _{IL} , MD1 = V _{IH}

Notes 1. V_{pp} must be under +13.5 V including overshoot.2. V_{DD} must be applied before V_{pp} on and must be off after V_{pp} off.

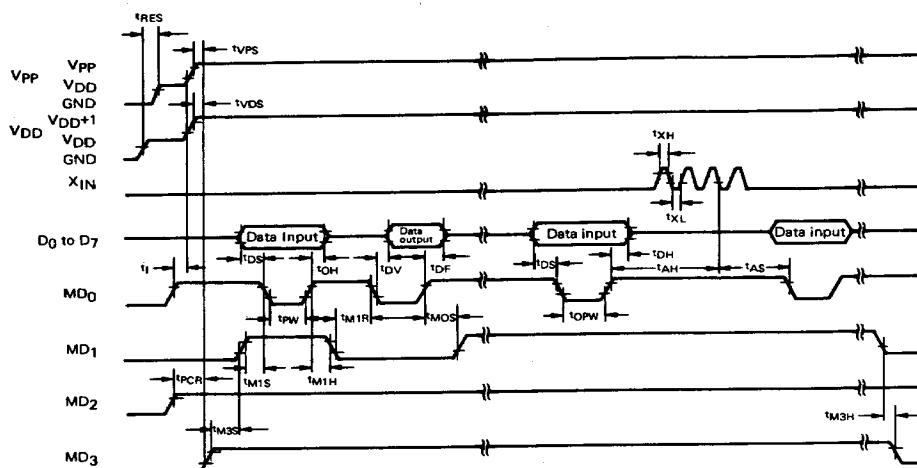
AC CHARACTERISTICS (T_a = 25 °C, V_{DD} = 6.0 ± 0.25 V, V_{PP} = 12.5 ± 0.5 V)

CHARACTERISTICS	SYMBOL	(*)	MIN.	TYP.	MAX.	UNIT	CONDITION
Address Set Up Time(*2) to MD0↓	t _{AS}	t _{AS}	2			μs	
MD1 Setup Time to MD0↓	t _{M1S}	t _{OES}	2			μs	
Data Setup Time to MD0↓	t _{DS}	t _{DS}	2			μs	
Address Hold Time(*2) to MD0↑	t _{AH}	t _{AH}	2			μs	
Data Hold Time to MD0↑	t _{DH}	t _{DH}	2			μs	
Data Output Float Delay Time from MD0↑→	t _{DF}	t _{DF}	0		130	ns	
V _{PP} Setup Time to MD3↑	t _{VPS}	t _{VPS}	2			μs	
V _{DD} Setup Time to MD3↑	t _{VDS}	t _{VCS}	2			μs	
Initial Program Pulse Width	t _{PW}	t _{PW}	0.95	1.0	1.05	ms	
Additional Program Pulse Width	t _{OPW}	t _{OPW}	0.95		21.0	ms	
MD0 Setup Time to MD1↑	t _{MOS}	t _{CES}	2			μs	
Data Output Delay Time from MD0↓→	t _{DV}	t _{DV}			1	μs	MD0 = MD1 = V _{IL}
MD1 Hold Time to MD0↑	t _{M1H}	t _{OEH}	2			μs	t _{M1H} + t _{M1R} ≥ 50 μs
MD1 Recovery Time to MD0↓	t _{M1R}	t _{OR}	2			μs	
Program Counter Reset Time	t _{PCR}	—	10			μs	
X _{IN} Input High, Low Level Range	t _{XH} , t _{XL}	—	0.063			μs	
X _{IN} Input Frequency	f _X	—			8	MHz	
Initial Mode Set Time	t _i	—	2			μs	
MD3 Setup Time to MD1↑	t _{M3S}	—	2			μs	
MD3 Hold Time to MD1↓	t _{M3H}	—	2			μs	
MD3 Setup Time to MD0↓	t _{M3SR}	—	2			μs	Read program memory
Data Output Delay Time from Address(*2)	t _{DAD}	t _{ACC}	2			μs	Read program memory
Data Output Hold Time from Address(*2)	t _{HAD}	t _{OH}	0		130	ns	Read program memory
MD3 Hold Time to MD0↑	t _{M3HR}	—	2			μs	Read program memory
Data Output Float Delay Time from MD3↓→	t _{DFR}	—	2			μs	Read program memory
Reset Setup Time	t _{RES}		10			μs	

*1 Symbols for corresponding μPD27C256.

*2 Internal address signal is incremented by one at the falling edge of the third X_{IN} input, and it is not connected to the pin.

WRITE PROGRAM MEMORY TIMING



READ PROGRAM MEMORY TIMING

